SMA　Fast Recovery Diode　快恢复二极管



■Features 特点

Glass Passivated Chip Junction 玻璃钝化芯片结
Fast Recovery time 快恢复时间
Surface mount device 表面贴装器件
Case 封装:SMA

■Maximum Rating 最大额定值

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	RS2AA	RS2BA	RS2DA	RS2GA	RS2JA	RS2KA	RS2M	Unit 单位
Marking 印字		RS2A	RS2B	RS2D	RS2G	RS2J	RS2K	RS2M	
Repetitive Peak Reverse Voltage 重复峰值反向电压	V_{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	V_R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I_F	2							A
Peak Surge Current 峰值浪涌电流	I_{FSM}	50							A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	65							℃/W
Operating/Storage Temperature 工作温度和储藏温度范围	T_J,T_{stg}	-65to+150							℃

■Electrical Characteristics 电特性

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	RS2AA-RS2GA	RS2JA	RS2KA-RS2MA	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F	1.3			V	I_F=2A
Reverse Current 反向电流	I_R	5(T_A=25℃) 300(T_A=125℃)			μA	V_R=V_{RRM}
Reverse Recovery Time 反向恢复时间	Trr	150	250	500	nS	I_F=0.5A,I_R=1A Irr=0.25A
Junction Capacitance 结电容	C_J	50			pF	V_R=4V,f=1MHz

■Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CHARACTERISTICS

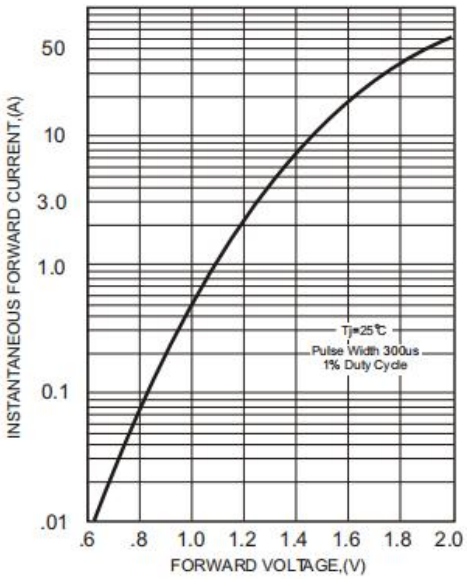


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

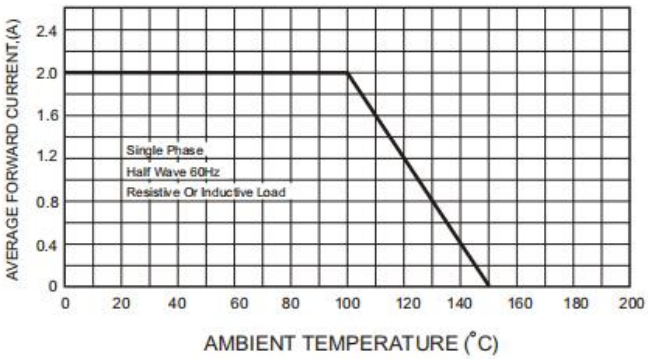
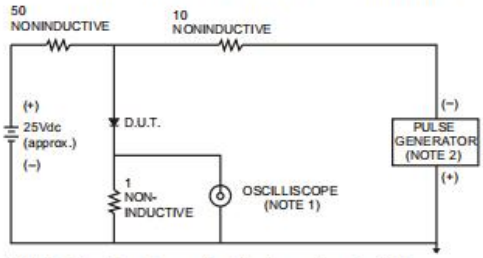


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.

2. Rise Time= 10ns max., Source Impedance= 50 ohms.

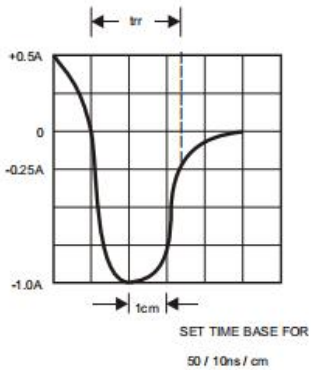


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

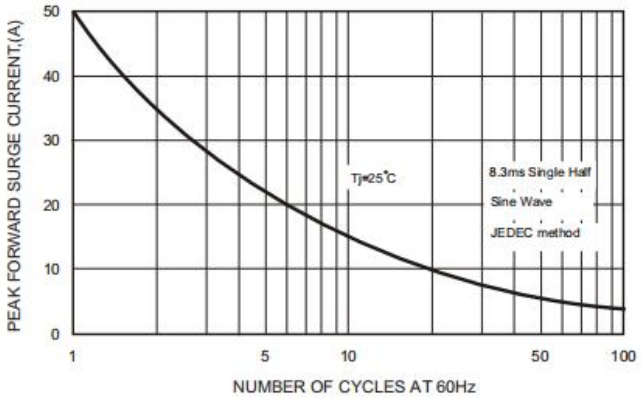
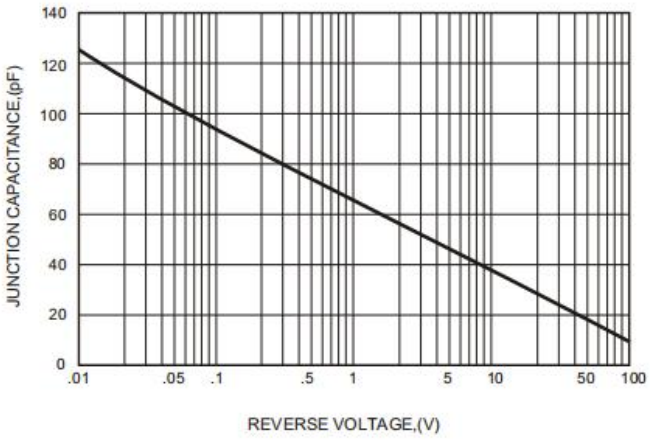
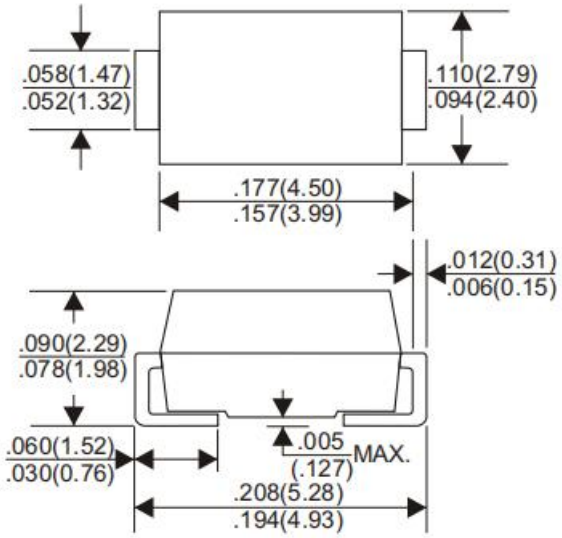


FIG.5-TYPICAL JUNCTION CAPACITANCE



■**Dimension 外形封装尺寸**

DO-214AC(SMA)



Dimensions in inches and (millimeters)